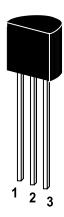
## **PNP Silicon Epitaxial Planar Transistor**

for high voltage applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings ( $T_a = 25^{\circ}C$ )

	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	150	V
Collector Emitter Voltage	-V <sub>CEO</sub>	150	V
Emitter Base Voltage	-V <sub>EBO</sub>	5	V
Collector Current	-I <sub>C</sub>	50	mA
Emitter Current	I <sub>E</sub>	50	mA
Power Dissipation	P <sub>tot</sub>	1000	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







## ST 2SA1024

## Characteristics at T<sub>amb</sub>=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V <sub>CE</sub> =5V, -I <sub>C</sub> =10mA					
Current Gain Group O	h <sub>FE</sub>	70	-	140	-
Y	h <sub>FE</sub>	120	-	240	-
Collector Cutoff Current					
at -V <sub>CB</sub> =150V	-I <sub>CBO</sub>	-	-	0.1	μΑ
Emitter Cutoff Current					
at -V <sub>EB</sub> =5V	-I <sub>EBO</sub>	-	-	0.1	μΑ
Gain Bandwidth Product					
at -V <sub>CE</sub> =30V, -I <sub>C</sub> =10mA	f <sub>T</sub>	-	120	-	MHz
Output Capacitance					
at -V <sub>CB</sub> =10V, f=1MHz	Сов	-	4	5	pF
Base Emitter Voltage					
at - $V_{CE}$ =5 $V$ , - $I_{C}$ =30 $mA$	-V <sub>BE</sub>	-	-	0.9	V
Collector Saturation Voltage					
at -I <sub>C</sub> =10mA, -I <sub>B</sub> =1mA	-V <sub>CE(sat)</sub>	-	-	0.8	V







